



FUKUCOM COMPANY LTD.

福 靈 有 限 公 司

FLAT P, 3/F., EVEREST INDUSTRIAL CENTRE, 396 KWUN TONG ROAD,
KWUN TONG, KOWLOON, HONG KONG.

TEL: 852-2790 0314 FAX: 852-2790 0206

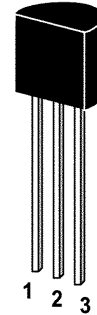
ST 2SC3202

NPN Silicon Epitaxial Planar Transistor

for switching and general purpose applications.

The transistor is subdivided into two groups, O and Y according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.

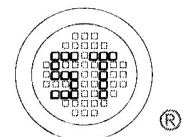


1. Emitter 2. Collector 3. Base

TO-92 Plastic Package
Weight approx. 0.19g

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	35	V
Collector Emitter Voltage	V_{CEO}	30	V
Emitter Base Voltage	V_{EBO}	5	V
Collector Current	I_{C}	500	mA
Emitter Current	I_{E}	-500	mA
Power Dissipation	P_{tot}	625	mW
Junction Temperature	T_{j}	150	$^\circ\text{C}$
Storage Temperature Range	T_{s}	-55 to +150	$^\circ\text{C}$



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Dated : 07/12/2002



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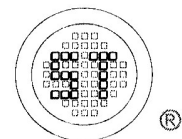
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Characteristics at $T_{amb}=25\text{ }^{\circ}\text{C}$

	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $V_{CE}=1\text{V}$, $I_C=100\text{mA}$					
Current Gain Group					
O	h_{FE}	70	-	140	-
Y	h_{FE}	120	-	240	-
at $V_{CE}=6\text{V}$, $I_C=400\text{mA}$					
O	h_{FE}	25	-	--	--
Y	h_{FE}	40	-	-	-
Collector Cutoff Current at $V_{CB}=35\text{V}$	I_{CBO}	-	-	0.1	μA
Emitter Cutoff Current at $V_{EB}=5\text{V}$	I_{EBO}	-	-	0.1	μA
Collector Emitter Saturation Voltage at $I_C=100\text{mA}$, $I_B=10\text{mA}$	$V_{CE(sat)}$	-	0.1	0.25	V
Base Emitter Voltage at $V_{CE}=1\text{V}$, $I_C=100\text{mA}$	V_{BE}	-	0.8	1	V
Transition Frequency at $V_{CE}=6\text{V}$, $I_C=20\text{mA}$	f_T	-	300	-	MHz
Collector Output Capacitance at $V_{CB}=6\text{V}$, $f=1\text{MHz}$	C_{OB}	-	7.0	-	pF



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